

L Number	Hits	Search Text	DB	Time stamp
-	70	((single near3 event near3 upset) SEU) near3 (resist\$3 imped\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 19:01
-	53	((((single near3 event near3 upset) SEU) near3 (resist\$3 imped\$3))) and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 18:51
-	33	((((single near3 event near3 upset) SEU) near3 (resist\$3 imped\$3))) and memory) and (sram)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 18:52
-	0	(((((single near3 event near3 upset) SEU) near3 (resist\$3 imped\$3))) and memory) and (sram)) and (program\$5 near4 (resist\$3 imped\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 18:52
-	73	((single near3 event near3 upset) SEU) near5 (resist\$3 imped\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 18:48
-	12	((((single near3 event near3 upset) SEU) near5 (resist\$3 imped\$3))) and ((resist\$3 imped\$3) near2 value)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 19:06
-	0	((((single near3 event near3 upset) SEU) near5 (resist\$3 imped\$3))) and (program\$5 with transistor with (resist\$3 imped\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 19:08
-	0	((((single near3 event near3 upset) SEU) near5 (resist\$3 imped\$3))) and (program\$5 near4 (resist\$3 imped\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 19:08
-	0	((((single near3 event near3 upset) SEU) near5 (resist\$3 imped\$3))) and (program\$5 near4 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 19:35
-	48814	resist\$3 near2 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 19:35
-	76238	transistor near3 resistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 19:50
-	59077	(control\$5 program\$5 adjust\$4 variable) with transistor with (resist\$4 imped\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 18:48
-	18885	(control\$5 program\$5 adjust\$4 variable) near4 transistor near4 (resist\$4 imped\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 18:48
-	838	(single near3 event near3 upset) or SEU	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/01 18:49

-	841	((single near3 event near3 upset) SEU)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 18:11
-	143	((((single near3 event near3 upset) SEU)) and memory and (resist\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 14:03
-	21	(US-6369630-\$ or US-6271568-\$ or US-6180984-\$ or US-6058041-\$ or US-5311070-\$ or US-5307142-\$ or US-5212108-\$ or US-5189598-\$ or US-4956814-\$ or US-6252433-\$ or US-6172907-\$ or US-5889431-\$ or US-5301146-\$ or US-5018102-\$ or US-4884238-\$ or US-6111780-\$ or US-5631863-\$ or US-4903094-\$).did. or (US-20020109230-\$).did. or (US-6278287-\$ or DE-3871945-\$).did.	USPAT; US-PGPUB; DERWENT	2003/08/18 15:36
-	7	((US-6369630-\$ or US-6271568-\$ or US-6180984-\$ or US-6058041-\$ or US-5311070-\$ or US-5307142-\$ or US-5212108-\$ or US-5189598-\$ or US-4956814-\$ or US-6252433-\$ or US-6172907-\$ or US-5889431-\$ or US-5301146-\$ or US-5018102-\$ or US-4884238-\$ or US-6111780-\$ or US-5631863-\$ or US-4903094-\$).did. or (US-20020109230-\$).did. or (US-6278287-\$ or DE-3871945-\$).did.) and ohm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/18 15:40
-	0	10/125,666	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/12/17 19:51
-	6400	resist\$3 adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 17:39
-	25	((control\$5 program\$5 adjust\$4 variable) with transistor with (resist\$4 impeded\$4)) and ((single near3 event near3 upset) or SEU)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 20:34
-	51	((single near3 event near3 upset) or SEU) and ((resist\$4 impeded\$5) near2 value)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 20:34
-	61	((((single near3 event near3 upset) SEU)) and ohm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 20:34
-	30	((single near3 event near3 upset) SEU) and ((var\$5 program\$5 adjust\$4) near3 (impedance resistance))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 20:34
-	19	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (transistor near3 resistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 20:34
-	6	(((((single near3 event near3 upset) SEU) near5 (resist\$3 impeded\$3))) and (resist\$3 adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 20:34

-	23	(US-6271568-\$ or US-6180984-\$ or US-6172907-\$ or US-5889431-\$ or US-5307142-\$ or US-5301146-\$ or US-5018102-\$ or US-4884238-\$ or US-6111780-\$ or US-6058041-\$ or US-5631863-\$ or US-5311070-\$ or US-5212108-\$ or US-5126279-\$ or US-4903094-\$ or US-6369630-\$ or US-4725875-\$ or US-6252433-\$ or US-5189598-\$ or US-4956814-\$).did. or (US-20020109230-\$).did. or (DE-3871945-\$ or US-6278287-\$).did.	USPAT; US-PGPUB; DERWENT	2004/10/19 16:15
-	2	((US-6271568-\$ or US-6180984-\$ or US-6172907-\$ or US-5889431-\$ or US-5307142-\$ or US-5301146-\$ or US-5018102-\$ or US-4884238-\$ or US-6111780-\$ or US-6058041-\$ or US-5631863-\$ or US-5311070-\$ or US-5212108-\$ or US-5126279-\$ or US-4903094-\$ or US-6369630-\$ or US-4725875-\$ or US-6252433-\$ or US-5189598-\$ or US-4956814-\$).did. or (US-20020109230-\$).did. or (DE-3871945-\$ or US-6278287-\$).did.) and (programmable near3 logic)	USPAT	2004/10/19 16:15